N-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	60V
● I_D	12A
● $R_{DS(ON)}$(at V_{GS}=10V)	8.5 mohm
● $R_{DS(ON)}$(at V_{GS}=4.5V)	12 mohm
● 100% EAS Tested	

EAS

Typical Performance Characteristics

Figure1. Output Characteristics

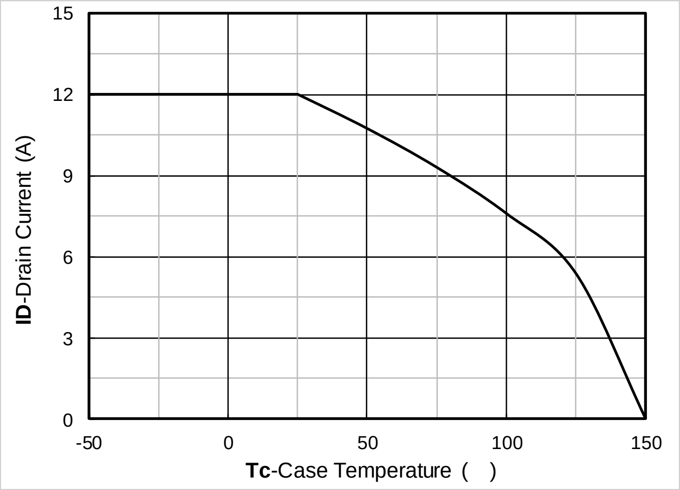

Figure7. Drain current

Figure8. Safe Operation Area

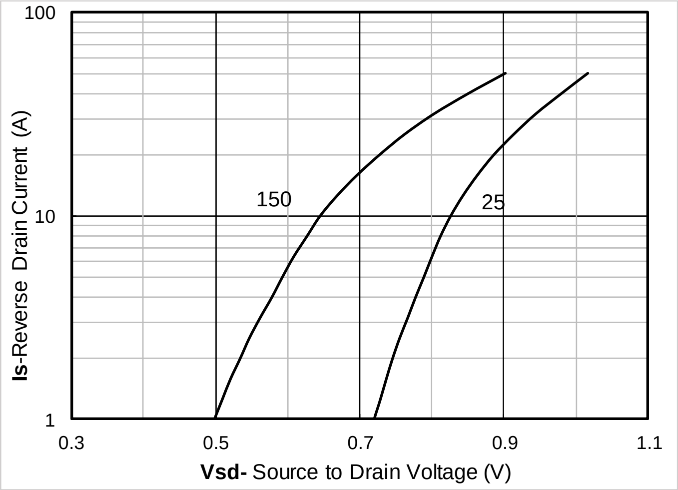

Figure 9. On-Resistance vs Gate to Source Voltage

Figure 10. Forward characteristics of reverse diode

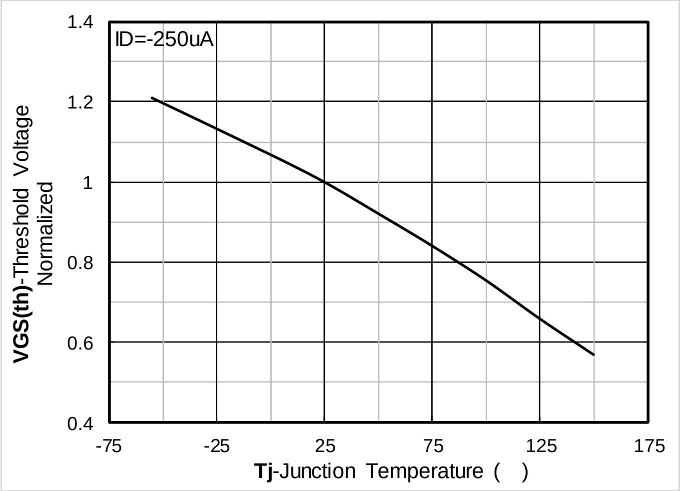

Figure 11. Normalized breakdown voltage

Figure 1

Figure

[redacted]